

IRFD024 Information

Part Number IRFD024

Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 2.5A 4-DIP

Package 4-DIP (0.300", 7.62mm)

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only

E-mail: salesdept@heisener.com



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IRFD024 Specifications

Manufacturer Part Number IRFD024 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 4-DIP (0.300", 7.62mm) Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 2.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 100 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)		
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds640pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds640pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C2.5A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds640pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds640pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	2.5A (Ta)
Gate Charge (Qg) (Max) @ Vgs 25nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 100 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 100 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.3W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	Gate Charge (Qg) (Max) @ Vgs	25nC @ 10V
FET Feature - Power Dissipation (Max) 1.3W (Ta) Rds On (Max) @ Id, Vgs 100 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Input Capacitance (Ciss) (Max) @ Vds	640pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 100 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs100 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device Package4-DIP, Hexdip, HVMDIPPackage / Case4-DIP (0.300", 7.62mm)	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Power Dissipation (Max)	1.3W (Ta)
Mounting Type Through Hole Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Rds On (Max) @ Id, Vgs	100 mOhm @ 1.5A, 10V
Supplier Device Package 4-DIP, Hexdip, HVMDIP Package / Case 4-DIP (0.300", 7.62mm)	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case 4-DIP (0.300", 7.62mm)	Mounting Type	Through Hole
	Supplier Device Package	4-DIP, Hexdip, HVMDIP
Report errors?	Package / Case	4-DIP (0.300", 7.62mm)
		Report errors?

IRFD024 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFD024 Payment Methods



















IRFD024 Shipping Methods













If you have any question about IRFD024, please do not hesitate to contact us!

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